

1/6

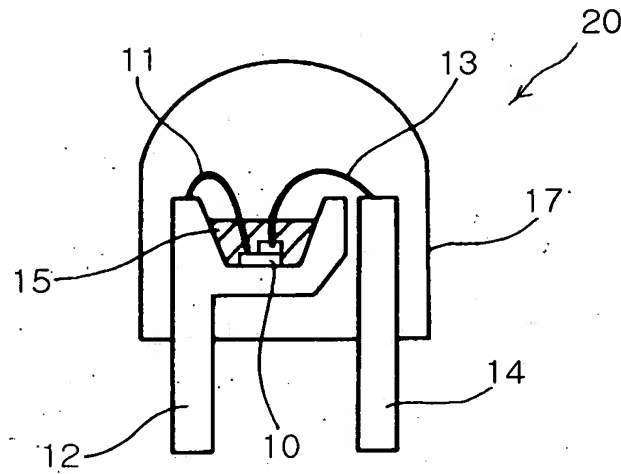


FIG. 1a  
PRIOR ART

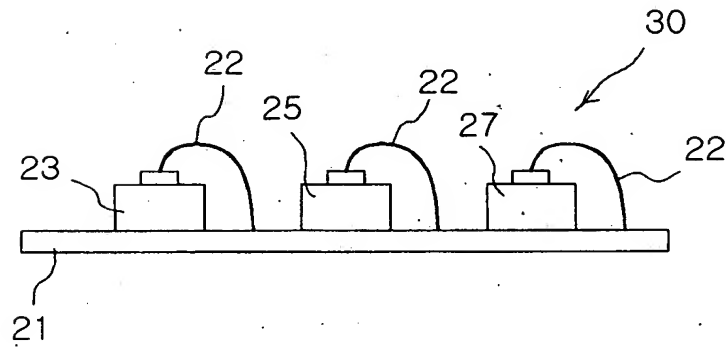


FIG. 1b  
PRIOR ART

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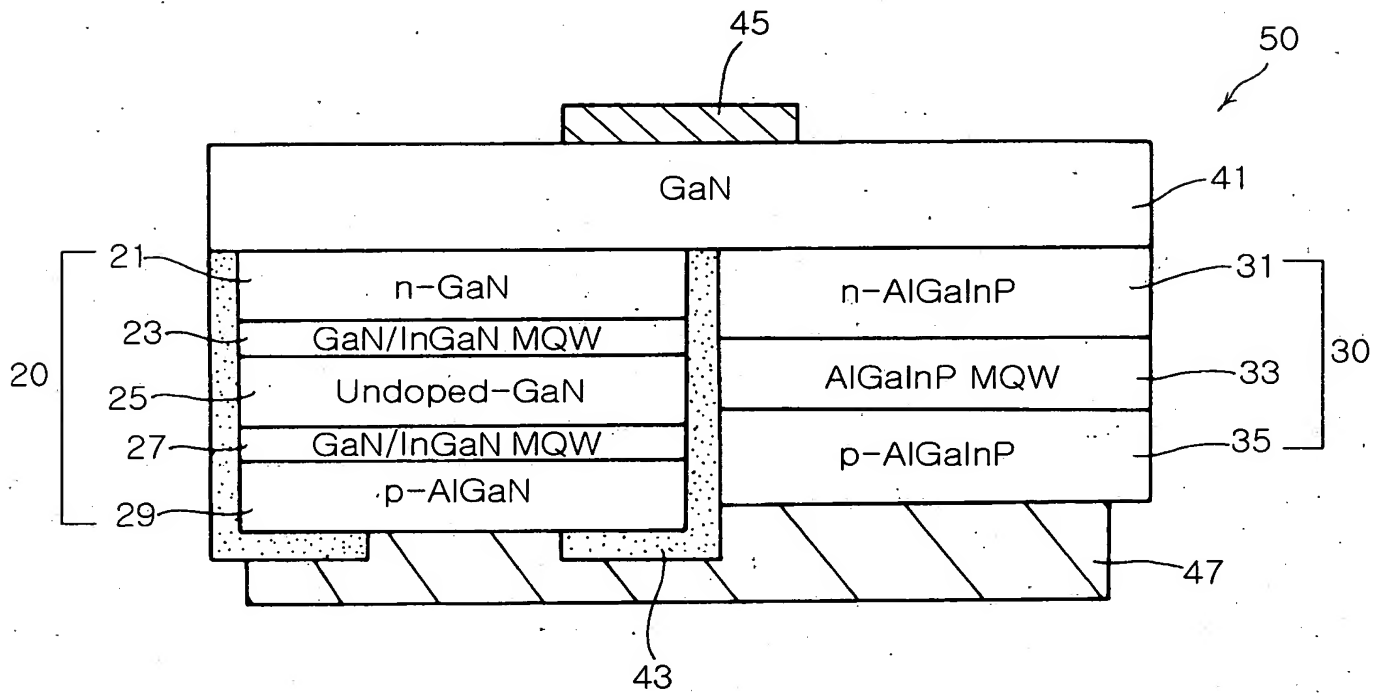


FIG. 2

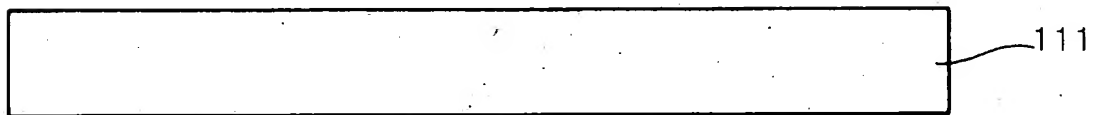


FIG. 3a

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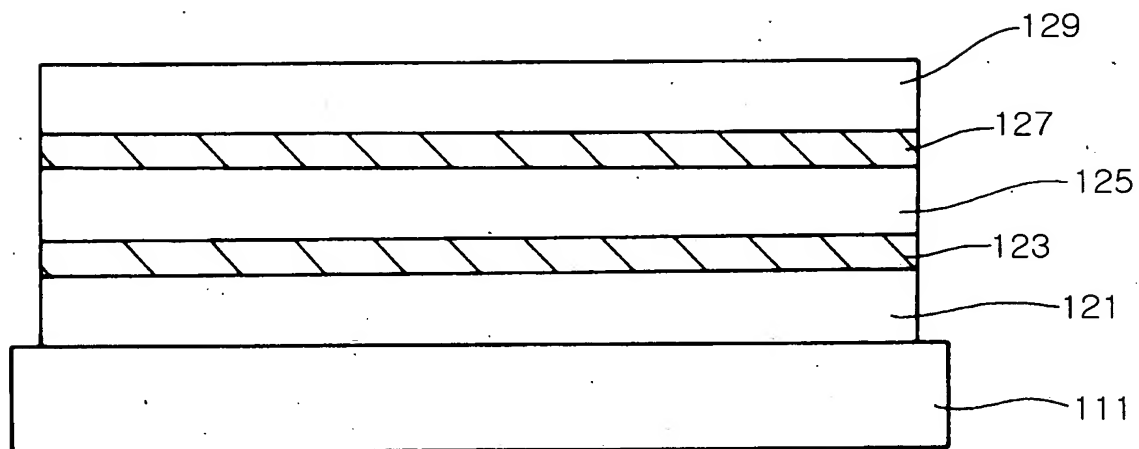


FIG. 3b

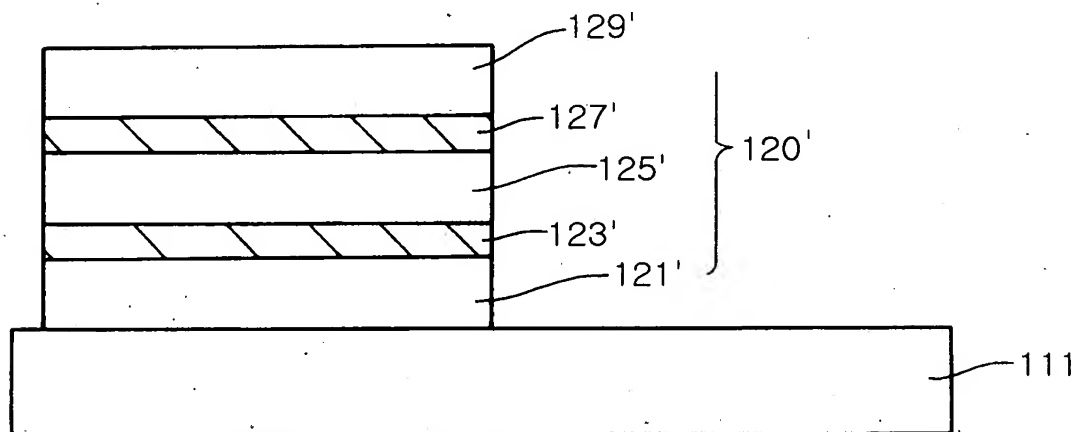


FIG. 3c

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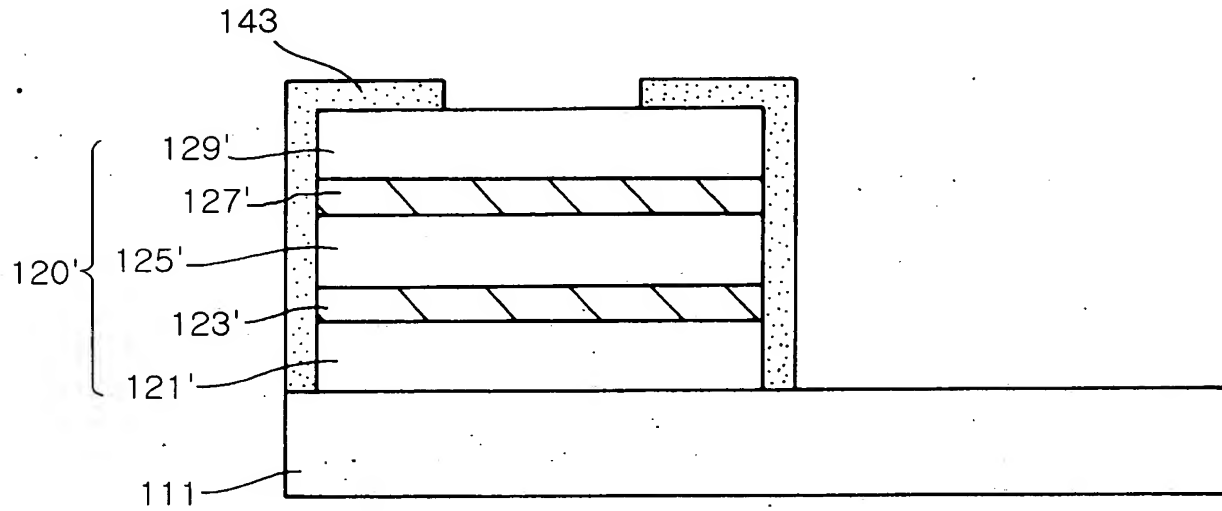


FIG. 3d

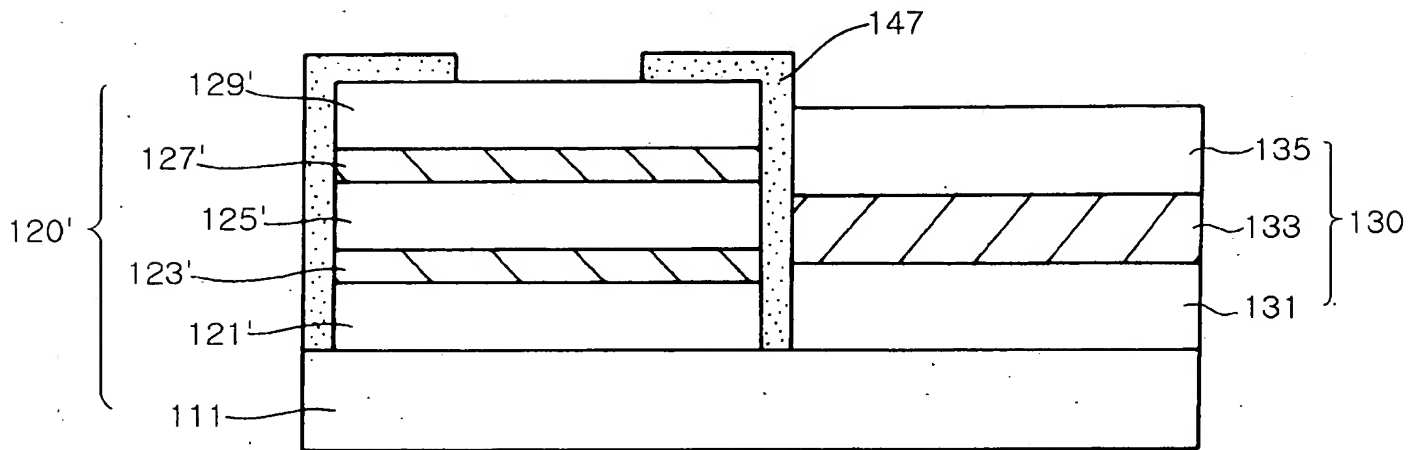


FIG. 3e

A cross-sectional view of a semiconductor device 200. The device features a substrate 151 with a top layer 185 and a central region 181. A vertical structure 183 is formed within the central region 181. A layer 170 is located below the central region 181. A layer 187 is at the bottom of the device. A vertical structure 194 is on the left side, with a positive terminal (+) indicated. A vertical structure 195 is on the right side, with a negative terminal (-) indicated. A layer 160a is on the left side, and a layer 160b is on the right side. A layer 196 is at the bottom of the device.

FIG. 4

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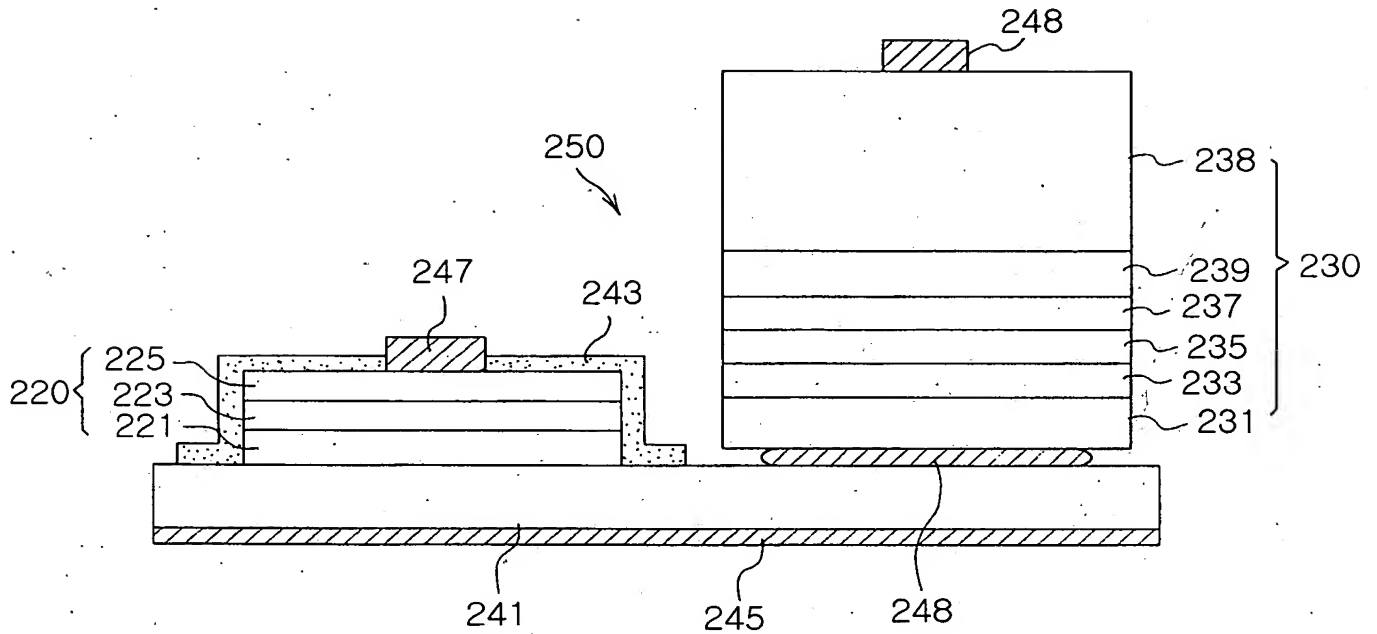


FIG. 5

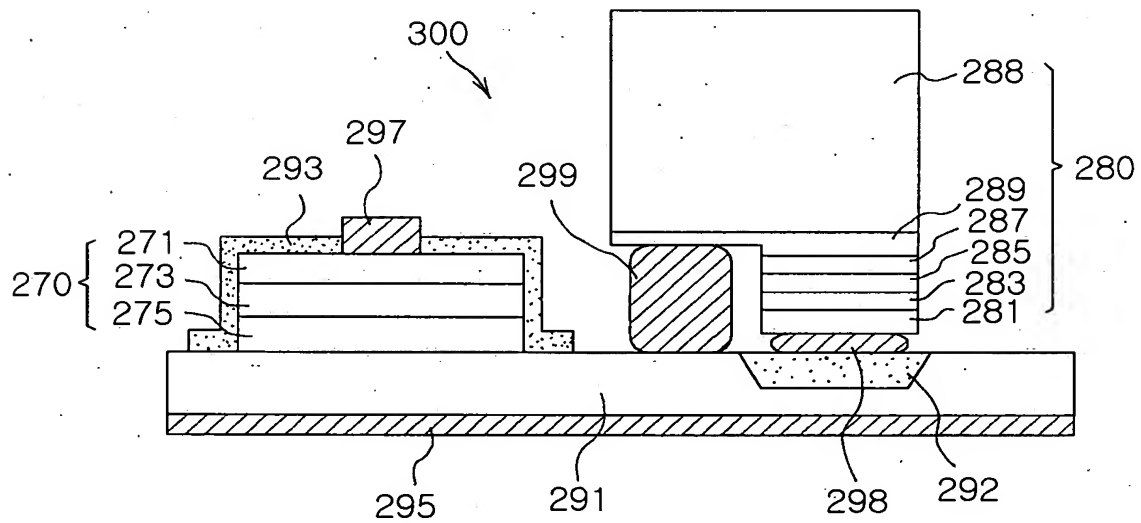


FIG. 6